

## LMT89 2.4V、10 $\mu$ A、SC70 温度传感器

### 1 特性

- 经济高效的热敏电阻替代产品
- 额定温度范围为 -55°C 至 130°C
- 采用 SC70 封装
- 可预计曲率误差
- 适合于远程应用

### 2 应用

- 工业
- 制热、通风与空调控制 (HVAC)
- 汽车
- 磁盘驱动器
- 便携式医疗仪器
- 计算机
- 电池管理
- 打印机
- 电源模块
- 传真机
- 移动电话
- 汽车

### 3 说明

LMT89 器件是一款高精度模拟输出 CMOS 集成电路温度传感器，工作温度范围为 -55°C 至 130°C。其工作电源范围为 2.4V 至 5.5V。LMT89 的传递函数主要是线性的，但有一个轻微可预测的抛物线曲率。当指定 LMT89 器件的传递函数为抛物线传递函数时，其在 30°C 的环境温度下的精度通常为  $\pm 1.5^\circ\text{C}$ 。温度误差线性增加，并且在极端温度范围时达到一个  $\pm 2.5^\circ\text{C}$  的最大值。此温度范围受电源电压的影响。当电源电压范围为 2.7V 至 5.5V 时，温度范围的上下限分别 130°C 和 -55°C。当电源电压降至 2.4V 时，下限值将变为 -30°C，而上限值将保持在 130°C。

LMT89 器件的静态电流不到 10 $\mu$ A。因此，在空气不流通的环境中，自发热不到 0.02°C。LMT89 本身具备关断功能，这是因为其自身功耗低，可直接通过许多逻辑门的输出供电，或者根本不需要关断。

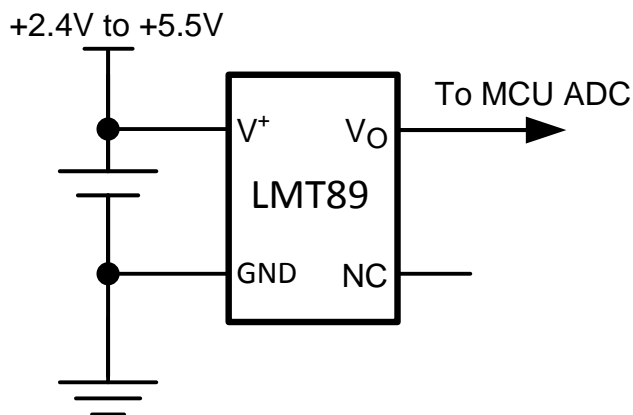
LMT89 器件是一款经济高效的热敏电阻替代产品。

#### 器件信息<sup>(1)</sup>

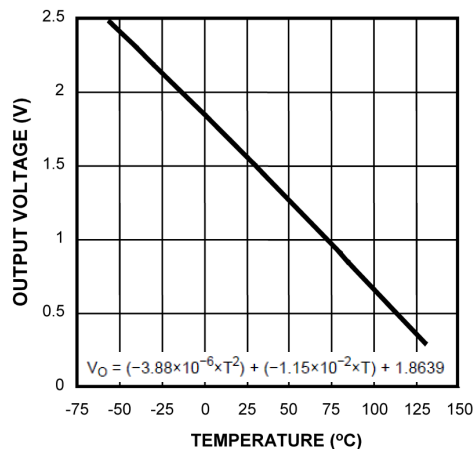
器件型号	封装	封装尺寸 (标称值)
LMT89	SOT (5)	2.00mm x 1.25mm

(1) 要了解所有可用封装，请见数据表末尾的可订购产品附录。

简化电路原理图



输出电压与温度间的关系



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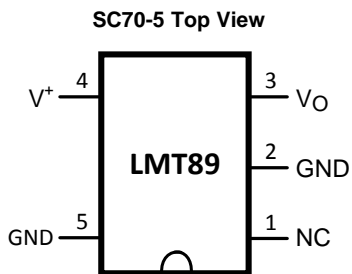
## 4 修订历史记录

### Changes from Original (March 2013) to Revision A

**Page**

- 已添加 引脚配置和功能部分, ESD 额定值表, 特性描述部分, 器件功能模式, 应用和实施部分, 电源相关建议部分, 布局部分, 器件和文档支持部分以及机械、封装和可订购信息部分..... **1**

## 5 Pin Configuration and Functions



### Pin Functions

PIN		I/O	DESCRIPTION
NO.	NAME		
1	NC	—	NC (pin 1) must be left floating or grounded. Other signal traces must not be connected to this pin.
2	GND	GND	Device substrate and die attach paddle, connect to power supply negative terminal. For optimum thermal conductivity to the PC board ground plane, pin 2 must be grounded. This pin may also be left floating.
3	$V_O$	Analog Output	Temperature sensor analog output
4	$V^+$	Power	Positive power supply pin
5	GND	GND	Device ground pin, connect to power supply negative terminal.

## 6 Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)(2)</sup>

	MIN	MAX	UNIT
Supply Voltage	-0.2	6.5	V
Output Voltage	(V <sup>+</sup> + 0.6 V)	-0.6	V
Output Current		10	mA
Input Current at any pin <sup>(3)</sup>	5		mA
Maximum Junction Temperature (T <sub>JMAX</sub> )		150	°C
Storage temperature (T <sub>stg</sub> )	-65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
- (2) Soldering process must comply with the Reflow Temperature Profile specifications. Refer to <http://www.ti.com/packaging>. Reflow temperature profiles are different for lead-free and non-lead-free packages.
- (3) When the input voltage (V<sub>I</sub>) at any pin exceeds power supplies (V<sub>I</sub> < GND or V<sub>I</sub> > V<sup>+</sup>), the current at that pin should be limited to 5 mA.

### 6.2 ESD Ratings

		VALUE	UNIT
V <sub>(ESD)</sub> <sup>(1)</sup> Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(2)</sup>	±2500	V
	Charged-device model (CDM), per JEDEC specification JESD22-C101 <sup>(3)</sup>	±250	

- (1) Accuracy is defined as the error between the measured and calculated output voltage at the specified conditions of voltage, current, and temperature (expressed in °C).
- (2) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (3) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	MAX	UNIT
LMT89 with 2.4 V ≤ V <sup>+</sup> ≤ 2.7 V	-30	130	°C
LMT89 with 2.7 V ≤ V <sup>+</sup> ≤ 5.5 V	-55	130	°C
Supply Voltage Range (V <sup>+</sup> )	2.4	5.5	V

### 6.4 Thermal Information

THERMAL METRIC <sup>(1)</sup>		LMT89	UNIT
		SOT	
		5 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	282	°C/W
R <sub>θJC(top)</sub>	Junction-to-case (top) thermal resistance	93	
R <sub>θJB</sub>	Junction-to-board thermal resistance	62	
Ψ <sub>JT</sub>	Junction-to-top characterization parameter	1.6	
Ψ <sub>JB</sub>	Junction-to-board characterization parameter	62	
R <sub>θJC(bot)</sub>	Junction-to-case (bottom) thermal resistance	—	

- (1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](http://www.ti.com/lit/an/spra953). For measured thermal resistance using specific printed circuit board layouts for the LMT89, see [Layout](#).

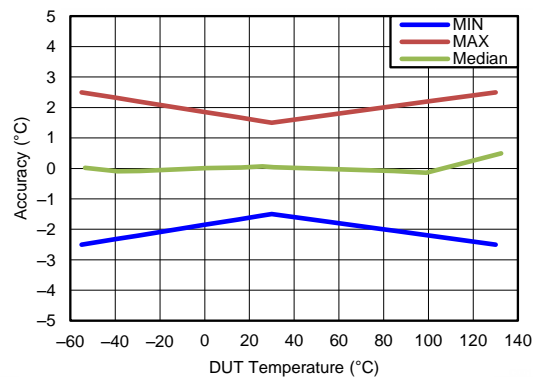
## 6.5 Electrical Characteristics

Unless otherwise noted, these specifications apply for  $V^+ = 2.7 V_{DC}$ . All limits  $T_A = T_J = T_{MIN}$  to  $T_{MAX}$ , unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN <sup>(1)</sup>	TYP <sup>(2)</sup>	MAX <sup>(1)</sup>	UNIT
Temperature to Voltage Error $V_O = (-3.88 \times 10^{-6} \times T^2) + (-1.15 \times 10^{-2} \times T) + 1.8639 V^{(3)}$		-2.5	±1.5	2.5	°C
Output Voltage at 0°C			1.8639		V
Variance from Curve			±1.0		°C
Non-Linearity <sup>(4)</sup>	$-20^\circ C \leq T_A \leq 80^\circ C$		±0.4%		
Sensor Gain (Temperature Sensitivity or Average Slope) to equation: $V_O = -11.77 mV/^\circ C \times T + 1.860 V$	$-30^\circ C \leq T_A \leq 100^\circ C$	-12.2	-11.77	-11.4	mV/°C
Output Impedance	Sourcing $I_L$ 0 $\mu A$ to 16 $\mu A$ <sup>(5)(6)</sup>			160	$\Omega$
Load Regulation <sup>(7)</sup>	Sourcing $I_L$ 0 $\mu A$ to 16 $\mu A$ <sup>(5)(6)</sup>			-2.5	mV
Line Regulation <sup>(8)</sup>	$2.4 V \leq V^+ \leq 5.0 V$			3.3	mV/V
	$5.0 V \leq V^+ \leq 5.5 V$			11	mV
Quiescent Current	$2.4 V \leq V^+ \leq 5.0 V; T_A = 25^\circ C$		4.5	7	$\mu A$
	$5.0 V \leq V^+ \leq 5.5 V; T_A = 25^\circ C$		4.5	9	$\mu A$
	$2.4 V \leq V^+ \leq 5.0 V$		4.5	10	$\mu A$
Change of Quiescent Current	$2.4 V \leq V^+ \leq 5.5 V$		0.7		$\mu A$
Temperature Coefficient of Quiescent Current			-11		nA/°C
Shutdown Current	$V^+ \leq 0.8 V$		0.02		$\mu A$

- (1) Limits are specified to TI's AOQL (Average Outgoing Quality Level).
- (2) Typical values are at  $T_J = T_A = 25^\circ C$  and represent most likely parametric norm.
- (3) Accuracy is defined as the error between the measured and calculated output voltage at the specified conditions of voltage, current, and temperature (expressed in °C).
- (4) Non-Linearity is defined as the deviation of the calculated output-voltage-versus-temperature curve from the best-fit straight line, over the temperature range specified.
- (5) The LMT89 can at most sink 1  $\mu A$  and source 16  $\mu A$ .
- (6) Load regulation or output impedance specifications apply over the supply voltage range of 2.4 V to 5.5 V.
- (7) Regulation is measured at constant junction temperature, using pulse testing with a low duty cycle. Changes in output due to heating effects can be computed by multiplying the internal dissipation by the thermal resistance.
- (8) Line regulation is calculated by subtracting the output voltage at the highest supply input voltage from the output voltage at the lowest supply input voltage.

## 6.6 Typical Characteristics



**Figure 1. Temperature Sensor Accuracy**

## 7 Detailed Description

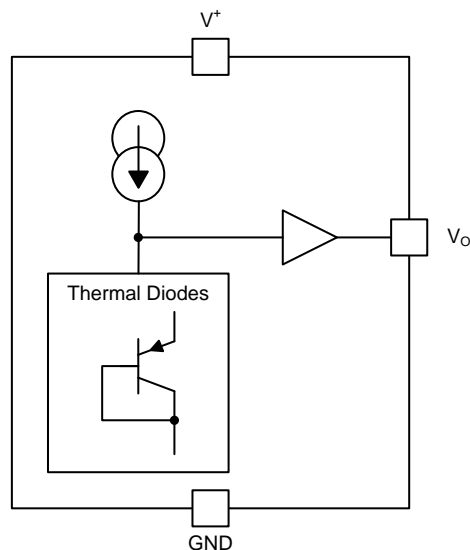
### 7.1 Overview

The LMT89 device is a precision analog output CMOS integrated-circuit temperature sensor that operates over a temperature range of  $-55^{\circ}\text{C}$  to  $130^{\circ}\text{C}$ . The power supply operating range is 2.4 V to 5.5 V. The transfer function of LMT89 is predominately linear, yet has a slight predictable parabolic curvature. The accuracy of the LMT89 device, when specified to a parabolic transfer function, is typically  $\pm 1.5^{\circ}\text{C}$  at an ambient temperature of  $30^{\circ}\text{C}$ . The temperature error increases linearly and reaches a maximum of  $\pm 5^{\circ}\text{C}$  at the temperature range extremes. The temperature range is affected by the power supply voltage. At a power supply voltage of 2.7 V to 5.5 V, the temperature range extremes are  $130^{\circ}\text{C}$  and  $-55^{\circ}\text{C}$ . Decreasing the power supply voltage to 2.4 V changes the negative extreme to  $-30^{\circ}\text{C}$ , while the positive remains at  $130^{\circ}\text{C}$ .

The LMT89 quiescent current is less than  $10\ \mu\text{A}$ . Therefore, self-heating is less than  $0.02^{\circ}\text{C}$  in still air. Shutdown capability for the LMT89 is intrinsic because its inherent low power consumption allows it to be powered directly from the output of many logic gates or does not necessitate shutdown at all.

The temperature sensing element is comprised of a simple base emitter junction that is forward biased by a current source. The temperature sensing element is then buffered by an amplifier and provided to the OUT pin. The amplifier has a simple class A output stage thus providing a low impedance output that can source  $16\ \mu\text{A}$  and sink  $1\ \mu\text{A}$ .

### 7.2 Functional Block Diagram



### 7.3 Feature Description

#### 7.3.1 LMT89 Transfer Function

The transfer function of the LMT89 device can be described in different ways with varying levels of precision. A simple linear transfer function with good accuracy near  $25^{\circ}\text{C}$  is shown in [Equation 1](#).

$$V_o = -11.69\ \text{mV}/^{\circ}\text{C} \times T + 1.8663\ \text{V} \quad (1)$$

Over the full operating temperature range of  $-55^{\circ}\text{C}$  to  $130^{\circ}\text{C}$ , best accuracy can be obtained by using the parabolic transfer function.

$$V_o = (-3.88 \times 10^{-6} \times T^2) + (-1.15 \times 10^{-2} \times T) + 1.8639 \quad (2)$$

Using [Equation 2](#) the following temperature to voltage output characteristic table can be generated.

**Feature Description (continued)**
**Table 1. Temperature to Voltage Output Characteristic Table**

TEMP (°C)	VOUT (V)	TEMP (°C)	VOUT (V)	TEMP (°C)	VOUT (V)	TEMP (°C)	VOUT (V)	TEMP (°C)	VOUT (V)	TEMP (°C)	VOUT (V)	TEMP (°C)	VOUT (V)
-55	2.4847	-28	2.1829	-1	1.8754	26	1.5623	53	1.2435	80	0.9191	107	0.5890
-54	2.4736	-27	2.1716	0	1.8639	27	1.5506	54	1.2316	81	0.9069	108	0.5766
-53	2.4625	-26	2.1603	1	1.8524	28	1.5389	55	1.2197	82	0.8948	109	0.5643
-52	2.4514	-25	2.1490	2	1.8409	29	1.5271	56	1.2077	83	0.8827	110	0.5520
-51	2.4403	-24	2.1377	3	1.8294	30	1.5154	57	1.1958	84	0.8705	111	0.5396
-50	2.4292	-23	2.1263	4	1.8178	31	1.5037	58	1.1838	85	0.8584	112	0.5272
-49	2.4181	-22	2.1150	5	1.8063	32	1.4919	59	1.1719	86	0.8462	113	0.5149
-48	2.4070	-21	2.1037	6	1.7948	33	1.4802	60	1.1599	87	0.8340	114	0.5025
-47	2.3958	-20	2.0923	7	1.7832	34	1.4684	61	1.1480	88	0.8219	115	0.4901
-46	2.3847	-19	2.0810	8	1.7717	35	1.4566	62	1.1360	89	0.8097	116	0.4777
-45	2.3735	-18	2.0696	9	1.7601	36	1.4449	63	1.1240	90	0.7975	117	0.4653
-44	2.3624	-17	2.0583	10	1.7485	37	1.4331	64	1.1120	91	0.7853	118	0.4529
-43	2.3512	-16	2.0469	11	1.7369	38	1.4213	65	1.1000	92	0.7731	119	0.4405
-42	2.3401	-15	2.0355	12	1.7253	39	1.4095	66	1.0880	93	0.7608	120	0.4280
-41	2.3289	-14	2.0241	13	1.7137	40	1.3977	67	1.0760	94	0.7486	121	0.4156
-40	2.3177	-13	2.0127	14	1.7021	41	1.3859	68	1.0640	95	0.7364	122	0.4032
-39	2.3065	-12	2.0013	15	1.6905	42	1.3741	69	1.0519	96	0.7241	123	0.3907
-38	2.2953	-11	1.9899	16	1.6789	43	1.3622	70	1.0399	97	0.7119	124	0.3782
-37	2.2841	-10	1.9785	17	1.6673	44	1.3504	71	1.0278	98	0.6996	125	0.3658
-36	2.2729	-9	1.9671	18	1.6556	45	1.3385	72	1.0158	99	0.6874	126	0.3533
-35	2.2616	-8	1.9557	19	1.6440	46	1.3267	73	1.0037	100	0.6751	127	0.3408
-34	2.2504	-7	1.9442	20	1.6323	47	1.3148	74	0.9917	101	0.6628	128	0.3283
-33	2.2392	-6	1.9328	21	1.6207	48	1.3030	75	0.9796	102	0.6505	129	0.3158
-32	2.2279	-5	1.9213	22	1.6090	49	1.2911	76	0.9675	103	0.6382	130	0.3033
-31	2.2167	-4	1.9098	23	1.5973	50	1.2792	77	0.9554	104	0.6259	—	—
-30	2.2054	-3	1.8984	24	1.5857	51	1.2673	78	0.9433	105	0.6136	—	—
-29	2.1941	-2	1.8869	25	1.5740	52	1.2554	79	0.9312	106	0.6013	—	—

Solving Equation 2 for T:

$$T = -1481.96 + \sqrt{2.1962 \times 10^6 + \frac{(1.8639 - V_O)}{3.88 \times 10^{-6}}} \quad (3)$$

For other methods of calculating T, see [Detailed Design Procedure](#).

## 7.4 Device Functional Modes

The only functional mode of the LMT89 device is that it has an analog output inversely proportional to temperature.

## 8 Application and Implementation

### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 8.1 Application Information

The LMT89 has a very low supply current and a wide supply range therefore it can easily be driven by a battery as shown in Figure 4.

#### 8.1.1 Capacitive Loads

The LMT89 device handles capacitive loading well. Without any precautions, the LMT89 device can drive any capacitive load less than 300 pF as shown in Figure 2. The specified temperature range the LMT89 device has a maximum output impedance of 160 Ω. In an extremely noisy environment it may be necessary to add some filtering to minimize noise pickup. TI recommends that 0.1 μF be added from V<sup>+</sup> to GND to bypass the power supply voltage, as shown in Figure 2. In a noisy environment it may even be necessary to add a capacitor from the output to ground with a series resistor as shown in Figure 2. A 1-μF output capacitor with the 160-Ω maximum output impedance and a 200-Ω series resistor will form a 442-Hz lowpass filter. Because the thermal time constant of the LMT89 device is much slower, the overall response time of the LMT89 device will not be significantly affected.

In situations where a transient load current is placed on the circuit output, the series resistance value may be increased to compensate for any ringing that may be observed.

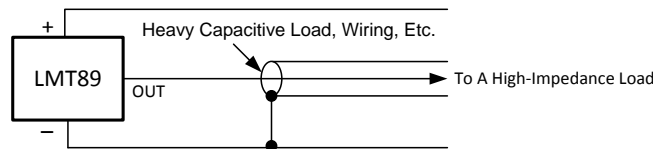


Figure 2. LMT89 No Decoupling Required for Capacitive Loads Less Than 300 pF

Table 2. Design Parameters

Minimum R (Ω)	C (μF)
200	1
470	0.1
680	0.01
1 k	0.001

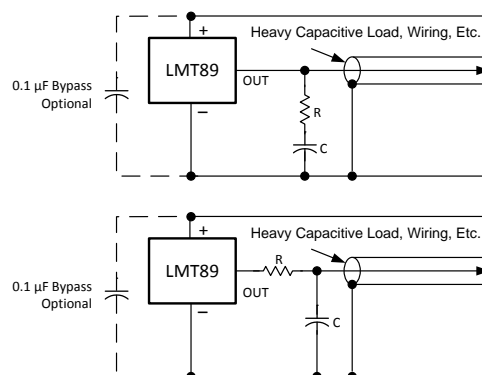


Figure 3. LMT89 With Filter for Noisy Environment and Capacitive Loading Greater Than 300 pF

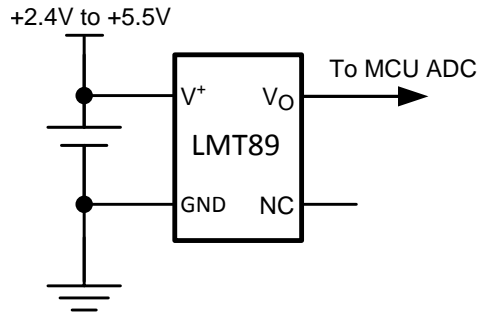


**NOTE**

Either placement of resistor, as shown in [Figure 2](#) and [Figure 3](#), is just as effective.

## 8.2 Typical Applications

### 8.2.1 Full-Range Centigrade Temperature Sensor



**Figure 4. Full-Range Celsius (Centigrade) Temperature Sensor (–55°C to 130°C) Operating from a Single Li-Ion Battery Cell**

#### 8.2.1.1 Design Requirements

Design requirements related to layout are also important because the LMT89 device is a simple temperature sensor that provides an analog output, refer to [Layout](#) for a detailed description.

#### 8.2.1.2 Detailed Design Procedure

The LMT89 device output is shown in [Equation 4](#).

$$V_O = (-3.88 \times 10^{-6} \times T^2) + (-1.15 \times 10^{-2} \times T) + 1.8639 \quad (4)$$

Solve for T as shown in [Equation 5](#):

$$T = -1481.96 + \sqrt{2.1962 \times 10^6 + \frac{(1.8639 - V_O)}{3.88 \times 10^{-6}}}$$

where

- T is temperature, and  $V_O$  is the measured output voltage of the LMT89 device. [Equation 5](#) is the most accurate equation that can be used to calculate the temperature of the LMT89 device. (5)

An alternative to the quadratic equation a second order transfer function can be determined using the least squares method shown in [Equation 6](#).

$$T = (-2.3654 \times V_O^2) + (-78.154 \times V_O) + 153.857$$

where

- T is temperature expressed in °C and  $V_O$  is the output voltage expressed in volts. (6)

A linear transfer function can be used over a limited temperature range by calculating a slope and offset that give best results over that range. A linear transfer function can be calculated from the parabolic transfer function of the LMT89 device. The slope of the linear transfer function can be calculated using [Equation 7](#).

$$m = -7.76 \times 10^{-6} \times T - 0.0115,$$

where

- T is the middle of the temperature range of interest and m is in V/°C. For example for the temperature range of  $T_{MIN} = -30$  to  $T_{MAX} = 100$ °C (7)

$$T = 35^\circ\text{C} \quad (8)$$

and

$$m = -11.77 \text{ mV}/^\circ\text{C} \quad (9)$$

### Typical Applications (continued)

The offset of the linear transfer function can be calculated using [Equation 10](#).

$$b = (V_{OP}(T_{MAX}) + V_{OP}(T) - m \times (T_{MAX} + T)) / 2$$

where

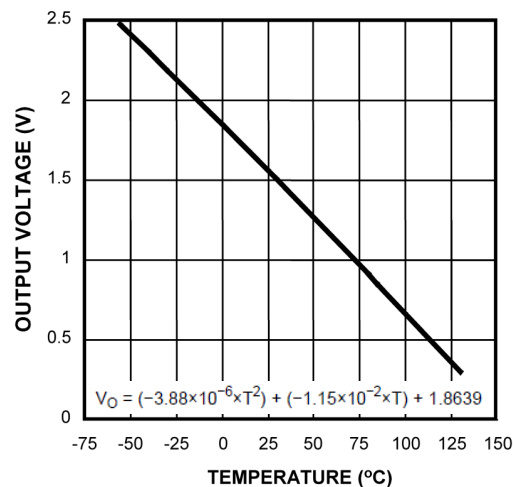
- $V_{OP}(T_{MAX})$  is the calculated output voltage at  $T_{MAX}$  using the parabolic transfer function for  $V_O$ .
- $V_{OP}(T)$  is the calculated output voltage at  $T$  using the parabolic transfer function for  $V_O$ . (10)

The best fit linear transfer function for many popular temperature ranges was calculated in [Table 3](#). As shown in [Table 3](#), the error introduced by the linear transfer function increases with wider temperature ranges.

**Table 3. First Order Equations Optimized for Different Temperature Ranges**

TEMPERATURE RANGE		LINEAR EQUATION	MAXIMUM DEVIATION OF LINEAR EQUATION FROM PARABOLIC EQUATION (°C)
$T_{min}$ (°C)	$T_{max}$ (°C)		
-55	130	$V_O = -11.79 \text{ mV/}^\circ\text{C} \times T + 1.8528 \text{ V}$	$\pm 1.41$
-40	110	$V_O = -11.77 \text{ mV/}^\circ\text{C} \times T + 1.8577 \text{ V}$	$\pm 0.93$
-30	100	$V_O = -11.77 \text{ mV/}^\circ\text{C} \times T + 1.8605 \text{ V}$	$\pm 0.70$
-40	85	$V_O = -11.67 \text{ mV/}^\circ\text{C} \times T + 1.8583 \text{ V}$	$\pm 0.65$
-10	65	$V_O = -11.71 \text{ mV/}^\circ\text{C} \times T + 1.8641 \text{ V}$	$\pm 0.23$
35	45	$V_O = -11.81 \text{ mV/}^\circ\text{C} \times T + 1.8701 \text{ V}$	$\pm 0.004$
20	30	$V_O = -11.69 \text{ mV/}^\circ\text{C} \times T + 1.8663 \text{ V}$	$\pm 0.004$

#### 8.2.1.3 Application Curve



**Figure 5. Output Voltage vs Temperature**

## 8.2.2 Centigrade Thermostat

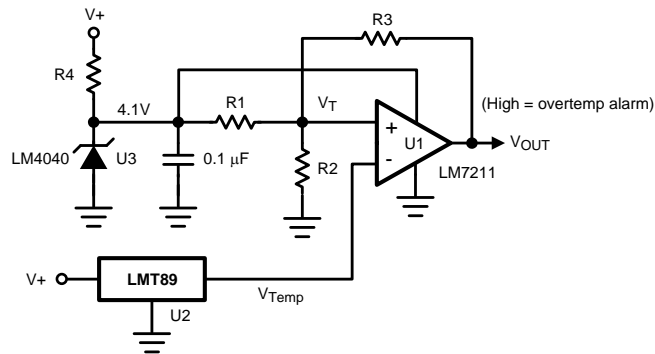


Figure 6. Centigrade Thermostat

### 8.2.2.1 Design Requirements

A simple thermostat can be created by using a reference (LM4040) and a comparator (LM7211) as shown in Figure 6.

### 8.2.2.2 Detailed Design Procedure

The threshold values can be calculated using Equation 11 and Equation 12.

$$V_{T1} = \frac{(4.1)R2}{R2 + R1 \parallel R3} \quad (11)$$

$$V_{T2} = \frac{(4.1)R2 \parallel R3}{R1 + R2 \parallel R3} \quad (12)$$

### 8.2.2.3 Application Curve

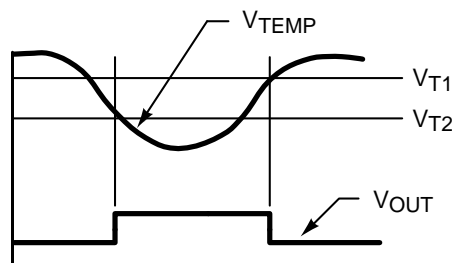


Figure 7. Thermostat Output Waveform

## 8.3 System Examples

### 8.3.1 Conserving Power Dissipation With Shutdown

The LMT89 device draws very little power therefore it can simply be shutdown by driving its supply pin with the output of an logic gate as shown in Figure 8.

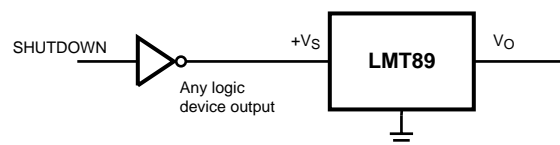
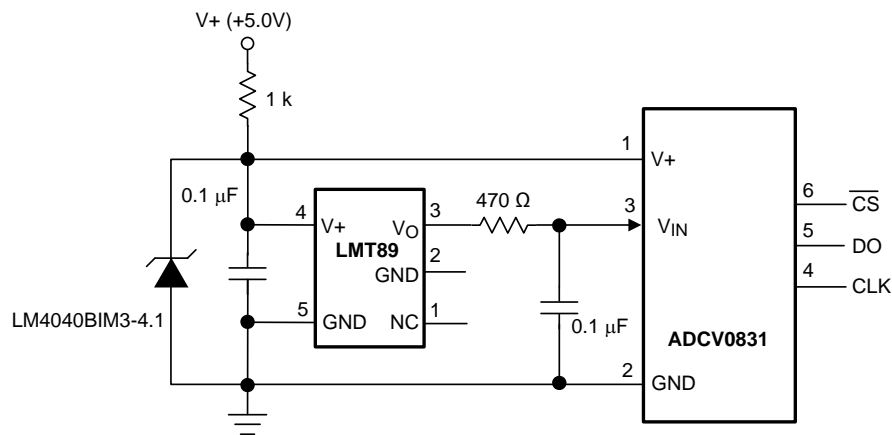


Figure 8. Conserving Power Dissipation With Shutdown

## System Examples (continued)

### 8.3.2 Analog-to-Digital Converter Input Stage

Most CMOS ADCs found in ASICs have a sampled data comparator input structure that is notorious for causing problems for analog output devices, such as the LMT89 and many op amps. The cause of this difficulty is the requirement of instantaneous charge of the input sampling capacitor in the ADC. This requirement is easily accommodated by the addition of a capacitor. Because not all ADCs have identical input stages, the charge requirements will vary necessitating a different value of compensating capacitor. This ADC is shown as an example only. If a digital output temperature is required, refer to devices such as the LM74 device.



**Figure 9. Suggested Connection to a Sampling Analog-to-Digital Converter Input Stage**

## 9 Power Supply Recommendations

The LMT89 device has a very wide 2.4-V to 5.5-V power supply voltage range making it ideal for many applications. In noisy environments, TI recommends adding at minimum 0.1  $\mu$ F from V<sup>+</sup> to GND to bypass the power supply voltage. Larger capacitances maybe required and are dependent on the power supply noise.

## 10 Layout

### 10.1 Layout Guidelines

The LMT89 device can be applied easily in the same way as other integrated-circuit temperature sensors. It can be glued or cemented to a surface. The temperature that the LMT89 device is sensing will be within about 0.02°C of the surface temperature to which the leads of the LMT89 device are attached.

This presumes that the ambient air temperature is almost the same as the surface temperature; if the air temperature were much higher or lower than the surface temperature, the actual temperature measured would be at an intermediate temperature between the surface temperature and the air temperature.

To ensure good thermal conductivity the backside of the LMT89 die is directly attached to the pin 2 GND pin. The temperatures of the lands and traces to the other leads of the LMT89 will also affect the temperature that is being sensed.

Alternatively, the LMT89 device can be mounted inside a sealed-end metal tube, and can then be dipped into a bath or screwed into a threaded hole in a tank. As with any IC, the LMT89 device and accompanying wiring and circuits must be kept insulated and dry, to avoid leakage and corrosion. This is especially true if the circuit may operate at cold temperatures where condensation can occur. Printed-circuit coatings and varnishes such as Humiseal and epoxy paints or dips are often used to ensure that moisture cannot corrode the LMT89 or its connections.

### Layout Guidelines (continued)

The thermal resistance junction to ambient ( $R_{\theta JA}$ ) is the parameter used to calculate the rise of a device junction temperature due to its power dissipation. Equation 13 is used to calculate the rise in the die temperature.

$$T_J = T_A + R_{\theta JA} [(V^+ I_Q) + (V^+ - V_O) I_L]$$

where

- $I_Q$  is the quiescent current and  $I_L$  is the load current on the output. Because the junction temperature of the LMT89 is the actual temperature being measured, take care to minimize the load current that the LMT89 device is required to drive. (13)

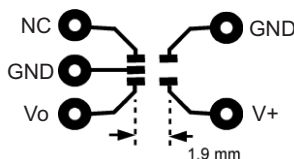
Table 4 summarizes the rise in die temperature of the LMT89 device (without any loading), and the thermal resistance for different conditions.

**Table 4. Temperature Rise of LMT89 Due to Self-Heating and Thermal Resistance ( $R_{\theta JA}$ )<sup>(1)</sup>**

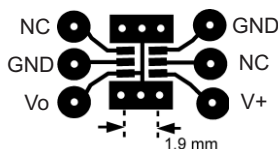
	SC70-5		SC70-5	
	NO HEAT SINK		SMALL HEAT SINK	
	$R_{\theta JA}$ (°C/W)	$T_J - T_A$ (°C)	$R_{\theta JA}$ (°C/W)	$T_J - T_A$ (°C)
Still air	412	0.2	350	0.19
Moving air	312	0.17	266	0.15

(1) See [Layout Examples](#) for PCB layout samples.

### 10.2 Layout Example



**Figure 10. Layout Used for No Heat Sink Measurements**



**Figure 11. Layout Used for Measurements With Small Heat Sink**

## 11 器件和文档支持

### 11.1 商标

All trademarks are the property of their respective owners.

### 11.2 静电放电警告



这些装置包含有限的内置 ESD 保护。存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

### 11.3 术语表

[SLYZ022](#) — TI 术语表。

这份术语表列出并解释术语、首字母缩略词和定义。

## 12 机械封装和可订购信息

以下页中包括机械封装和可订购信息。 这些信息是针对指定器件可提供的最新数据。 这些数据会在无通知且不对本文档进行修订的情况下发生改变。 欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LMT89DCKR	ACTIVE	SC70	DCK	5	3000	RoHS & Green	SN	Level-1-260C-UNLIM	-55 to 130	T3B	Samples
LMT89DCKT	OBSOLETE	SC70	DCK	5		TBD	Call TI	Call TI	-55 to 130	T3B	

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

**Green:** TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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**TAPE AND REEL INFORMATION**

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LMT89DCKR	SC70	DCK	5	3000	178.0	8.4	2.25	2.45	1.2	4.0	8.0	Q3



**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LMT89DCKR	SC70	DCK	5	3000	208.0	191.0	35.0

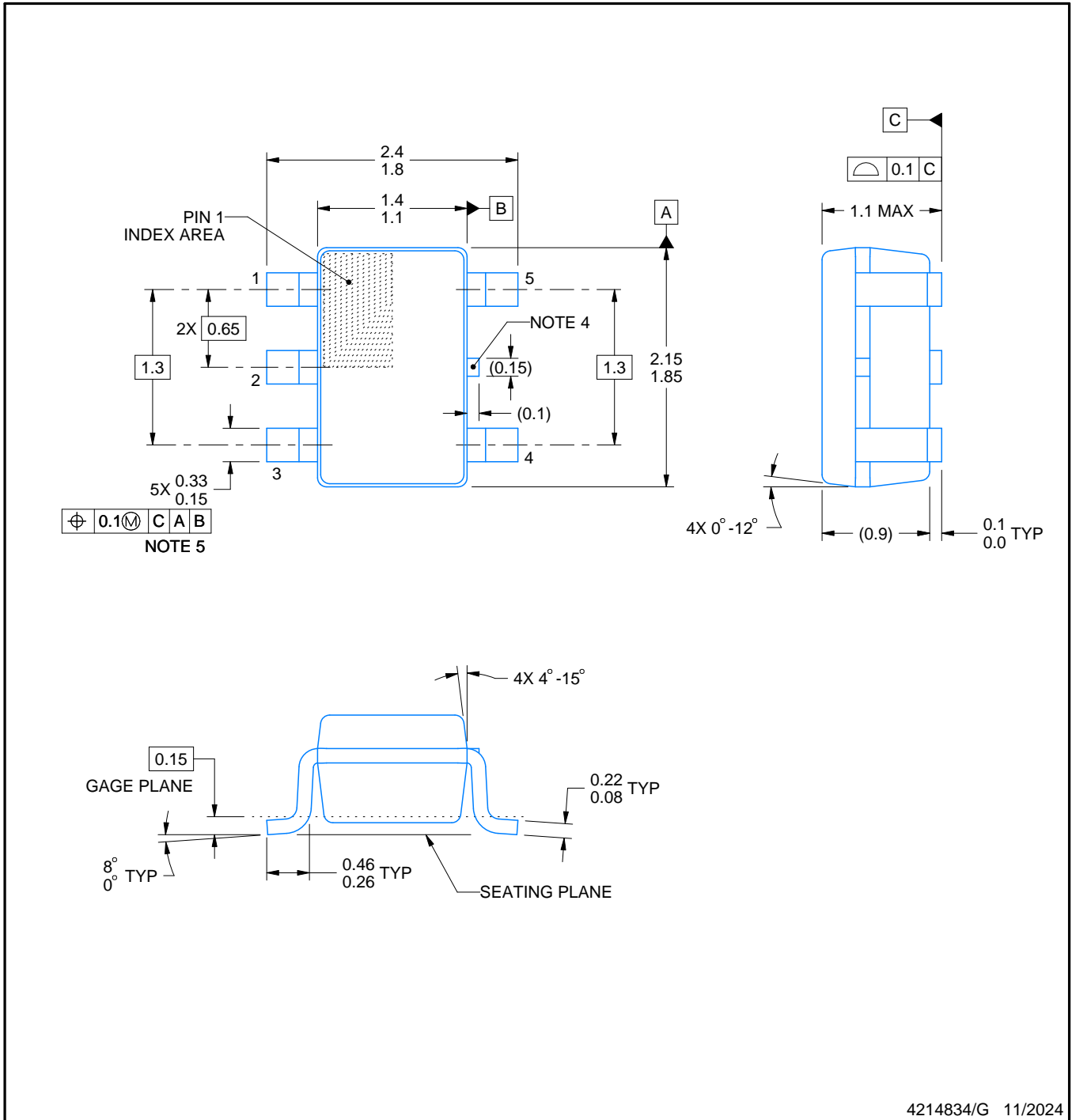
# DCK0005A



# PACKAGE OUTLINE

## SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



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**NOTES:**

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Reference JEDEC MO-203.
4. Support pin may differ or may not be present.
5. Lead width does not comply with JEDEC.
6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side

# EXAMPLE BOARD LAYOUT

DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



LAND PATTERN EXAMPLE  
EXPOSED METAL SHOWN  
SCALE:18X



SOLDER MASK DETAILS

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NOTES: (continued)

- 7. Publication IPC-7351 may have alternate designs.
- 8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

# EXAMPLE STENCIL DESIGN

DCK0005A

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



SOLDER PASTE EXAMPLE  
BASED ON 0.125 THICK STENCIL  
SCALE:18X

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NOTES: (continued)

9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
10. Board assembly site may have different recommendations for stencil design.

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